

Description

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

General Features

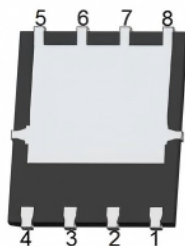
- $V_{DS} = 30V, I_D = 170A$
 $R_{DS(ON)} = 1.3m\Omega$ (typical) @ $V_{GS} = 10V$
 $R_{DS(ON)} = 1.9m\Omega$ (typical) @ $V_{GS} = 4.5V$
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 150 °C operating temperature
- Pb-free lead plating **100% UIS TESTED!**

100% ΔV_{ds} TESTED!

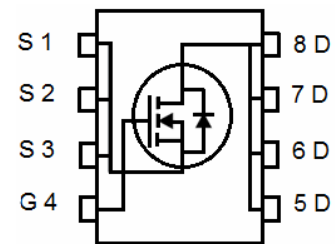
DFN 5X6



Top View



Bottom View



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
P015N30GU	RSTP015N30GU	DFN5X6-8L	-	-	-

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	170	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D (100^\circ C)$	130	A
Pulsed Drain Current	I_{DM}	680	A
Maximum Power Dissipation	P_D	95	W
Derating factor		0.76	W/°C
Single pulse avalanche energy ^(Note 5)	E_{AS}	583	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	1.31	°C/W
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Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	30		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	1.0	1.6	2.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =85A	-	1.3	1.5	mΩ
		V _{GS} =4.5V, I _D =85A	-	1.9	2.3	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V,I _D =85A	65	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =15V,V _{GS} =0V, F=1.0MHz	-	2988.1	-	PF
Output Capacitance	C _{oss}		-	1407.8	-	PF
Reverse Transfer Capacitance	C _{rss}		-	100.8	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =15V,I _D =85A V _{GS} =10V,R _G =1.6Ω	-	5.5	-	nS
Turn-on Rise Time	t _r		-	7.5	-	nS
Turn-Off Delay Time	t _{d(off)}		-	33.0	-	nS
Turn-Off Fall Time	t _f		-	5.0	-	nS
Total Gate Charge	Q _g	V _{DS} =15V,I _D =85A, V _{GS} =10V	-	46.1	-	nC
Gate-Source Charge	Q _{gs}		-	5.7		nC
Gate-Drain Charge	Q _{gd}		-	9.2		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =85A	-		1.2	V
Diode Forward Current (Note 2)	I _S		-	-	170	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = I _S	-	16	-	nS
Reverse Recovery Charge	Q _{rr}	di/dt = 100A/μs (Note3)	-	28	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition : $T_J=25^{\circ}\text{C}, V_{DD}=20V, V_G=10V, L=0.5\text{mH}, R_G=25\Omega$

Pb Free Product

Typical Electrical and Thermal Characteristics

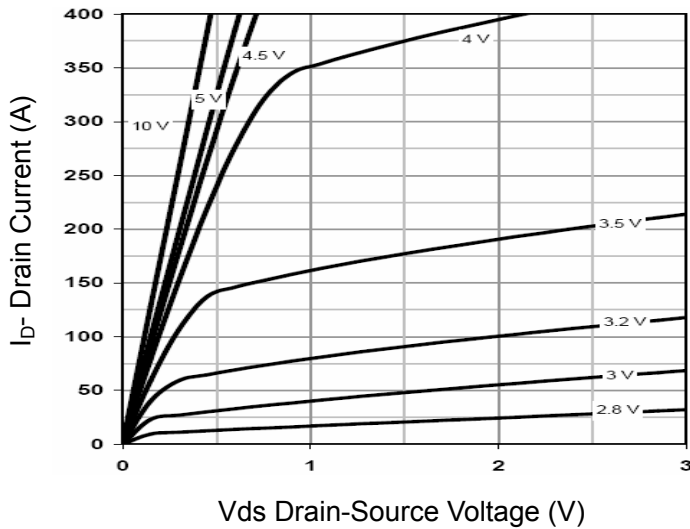


Figure 1 Output Characteristics

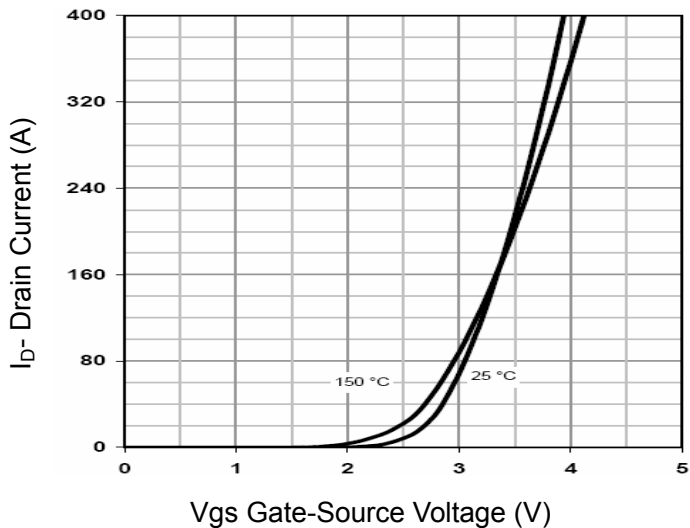


Figure 2 Transfer Characteristics

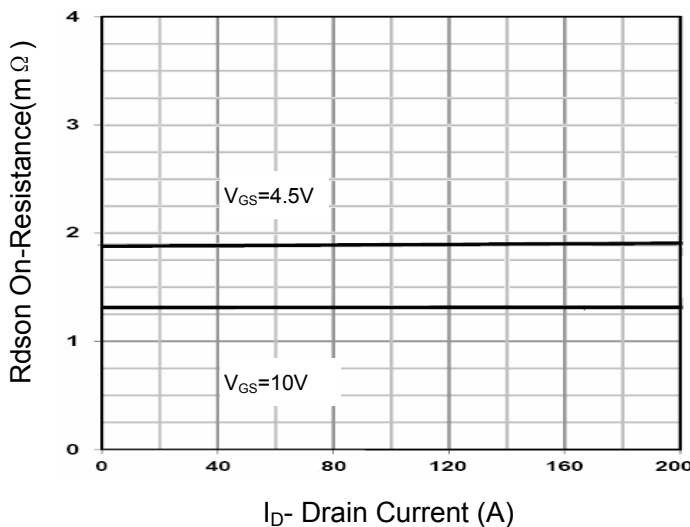


Figure 3 $R_{DS(on)}$ - Drain Current

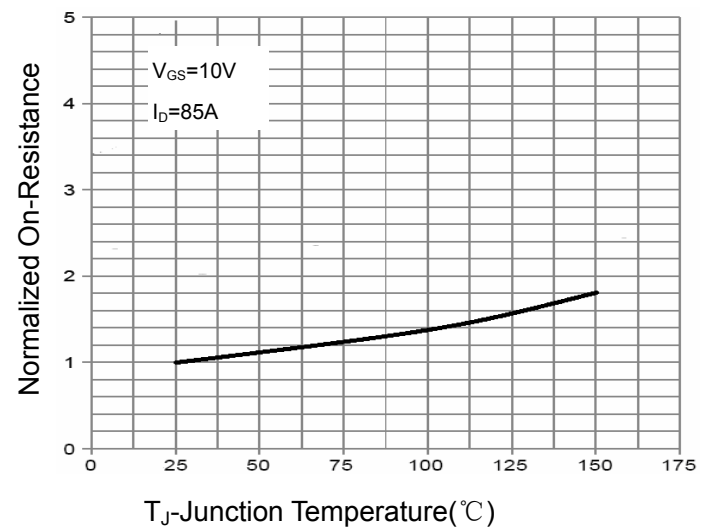


Figure 4 $R_{DS(on)}$ -Junction Temperature

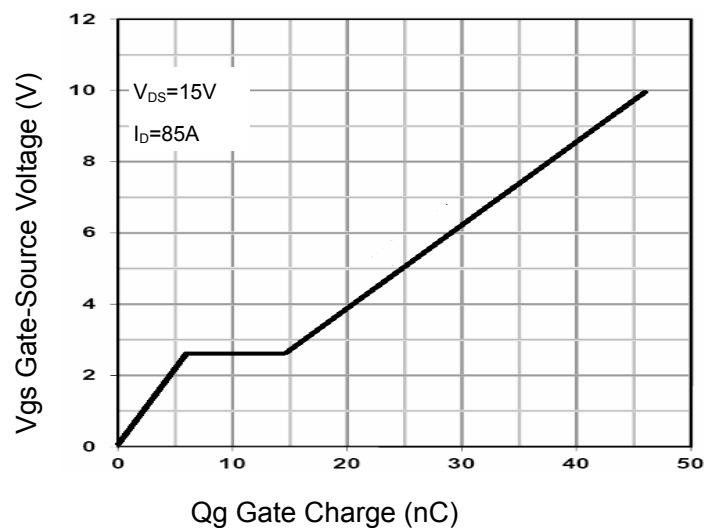


Figure 5 Gate Charge

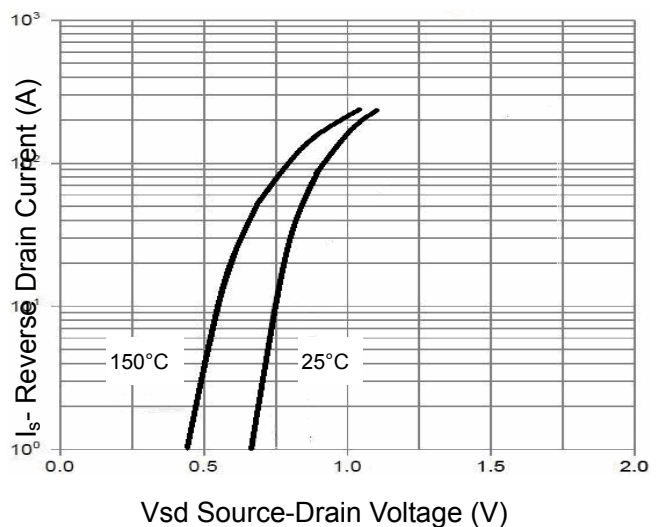
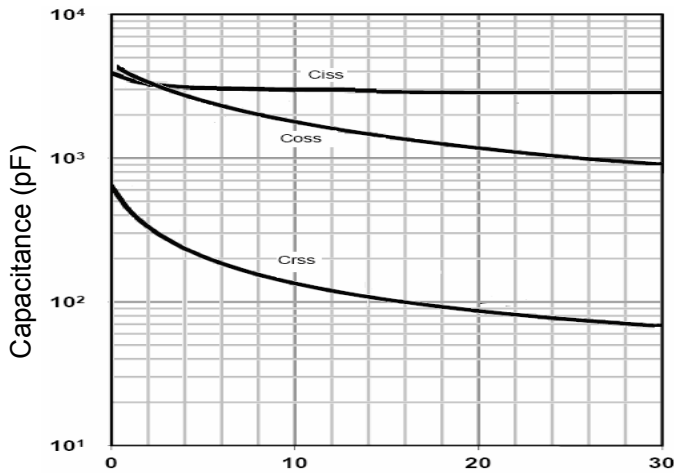
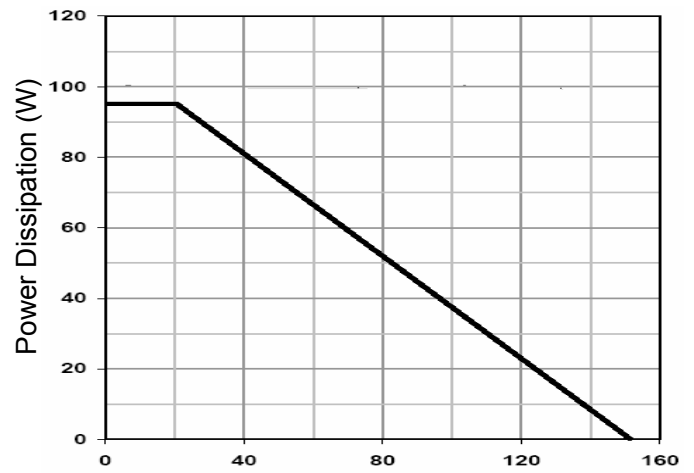


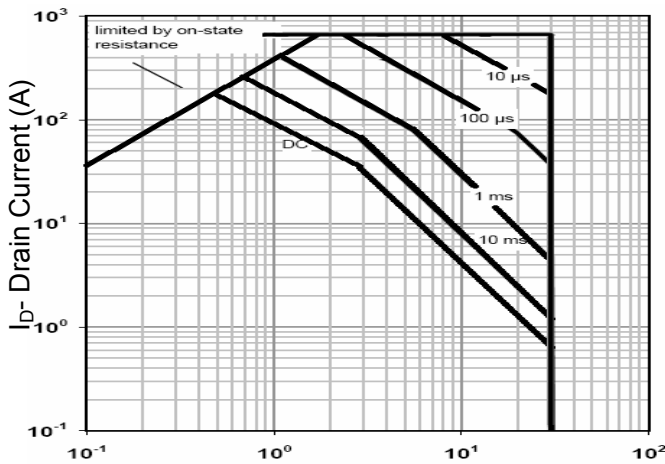
Figure 6 Source- Drain Diode Forward



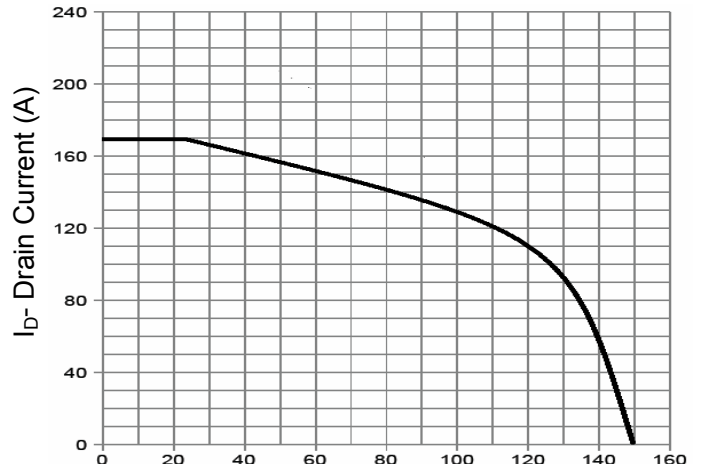
Vds Drain-Source Voltage (V)
Figure 7 Capacitance vs Vds



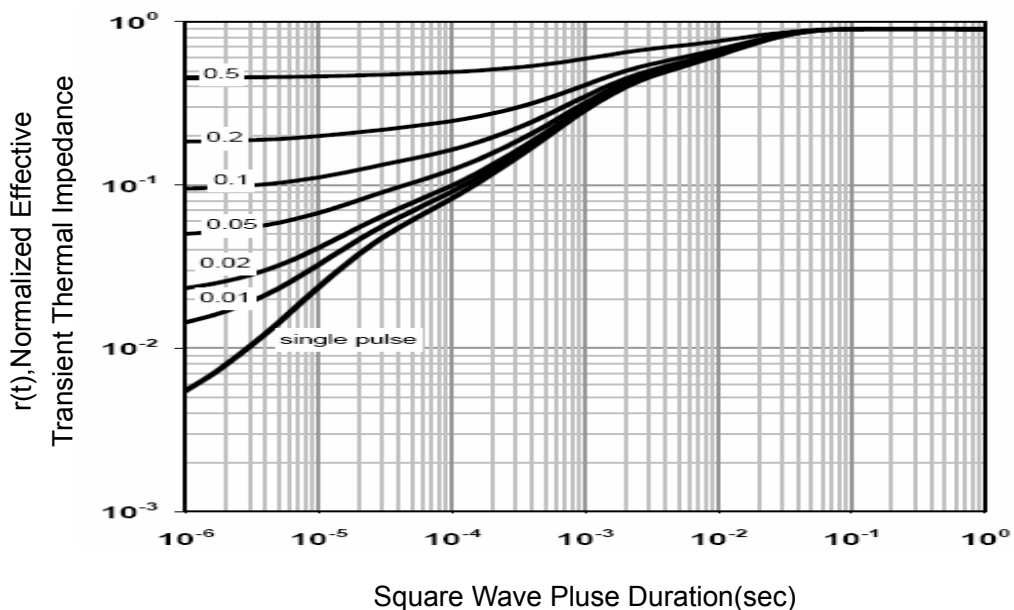
TJ-Junction Temperature(°C)
Figure 9 Power De-rating



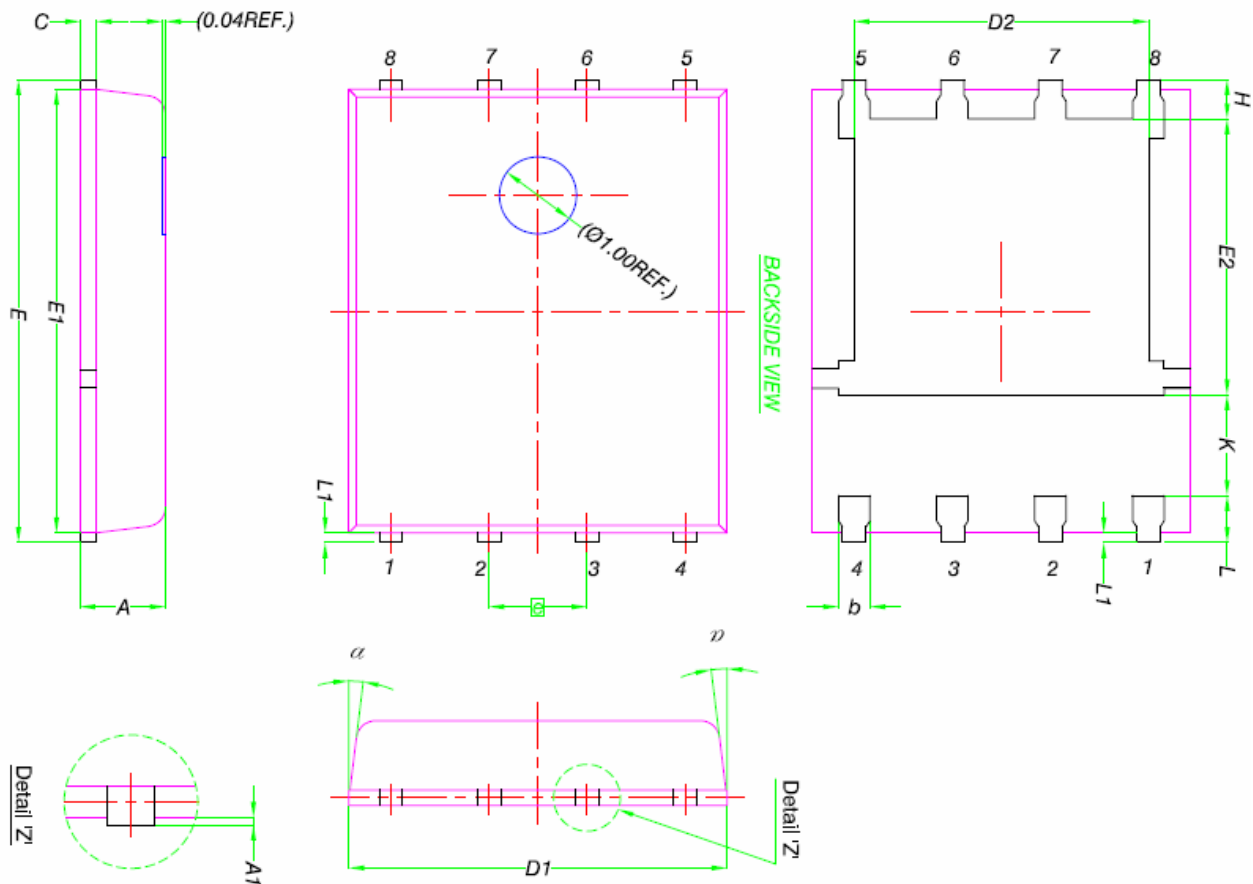
Vds Drain-Source Voltage (V)
Figure 8 Safe Operation Area



TJ-Junction Temperature (°C)
Figure 10 Current De-rating



Square Wave Pluse Duration(sec)
Figure 11 Normalized Maximum Transient Thermal Impedance

DFN5X6-8L Package Information
Pb Free Product


DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	-	0.05
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.27 BSC		
H	0.41	0.51	0.61
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
α	0°	-	12°

**Land Pattern
(Only for Reference)**
